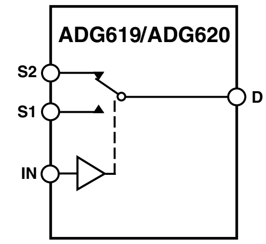
CMOS ±5 V/+5 V 4 Ω Single SPDT Switches

ADG619/ADG620

FEATURES
6 Ω (Max) On Resistance
0.8 Ω (Max) On-Resistance Flatness
2.7 V to 5.5 V Single Supply
±2.7 V to ±5.5 V Dual Supply
Rail-to-Rail Operation
8-Lead SOT-23 Package, 8-Lead Micro-SOIC Package
Typical Power Consumption (<0.1 μW)
TTL/CMOS Compatible Inputs

APPLICATIONS
Automatic Test Equipment
Power Routing
Communication Systems
Data Acquisition Systems
Sample and Hold Systems
Avionics
Relay Replacement
Battery-Powered Systems

FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC "1" INPUT

GENERAL DESCRIPTION

The ADG619 and the ADG620 are monolithic, CMOS SPDT (single pole, double throw) switches. Each switch conducts equally well in both directions when on.

The ADG619/ADG620 offers low On-Resistance of 4 Ω, which is matched to within 0.7 Ω between channels. These switches also provide low power dissipation yet give high switching speeds.The ADG619 exhibits break-before-make switching action, thus preventing momentary shorting when switching channels. The ADG620 exhibits make-before-break action.

The ADG619/ADG620 are available in 8-lead SOT-23 packages and 8-lead Micro-SOIC packages.

Table I. Truth Table for the ADG619/ADG620

IN	Switch S1	Switch S2
0	ON	OFF
1	OFF	ON

PRODUCT HIGHLIGHTS

1. Low On Resistance (R_{ON}) (4 Ω typ)
2. Dual ±2.7 V to ±5.5 V or Single 2.7 V to 5.5 V
3. Low Power Dissipation. CMOS construction ensures low power dissipation.
4. Fast t_{ON}/t_{OFF}
5. Tiny 8-Lead SOT-23 Package and 8-Lead Micro-SOIC Package

REV. 0

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ADG619/ADG620–SPECIFICATIONS

DUAL SUPPLY[1] (V_{DD} = +5 V ± 10%, V_{SS} = –5 V ± 10%, GND = 0 V. All specifications –40°C to +85°C unless otherwise noted.)

Parameter	B Version +25°C	B Version –40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		V_{SS} to V_{DD}	V	V_{DD} = +4.5 V, V_{SS} = –4.5 V
On Resistance (R_{ON})	4		Ω typ	V_S = ±4.5 V, I_S = –10 mA,
	6	8	Ω max	Test Circuit 1
On Resistance Match Between Channels (ΔR_{ON})	0.7		Ω typ	V_S = ±4.5 V, I_S = –10 mA
	1.1	1.35	Ω max	
On-Resistance Flatness ($R_{FLAT(ON)}$)	0.7	0.8	Ω typ	V_S = ±3.3 V, I_S = –10 mA
		1.2	Ω max	
LEAKAGE CURRENTS				V_{DD} = +5.5 V, V_{SS} = –5.5 V
Source OFF Leakage I_S (OFF)	±0.01		nA typ	V_S = ±4.5 V, V_D = ∓4.5 V,
	±0.25	±1	nA max	Test Circuit 2
Channel ON Leakage I_D, I_S (ON)	±0.01		nA typ	V_S = V_D = ±4.5 V, Test Circuit 3
	±0.25	±1	nA max	
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current				
I_{INL} or I_{INH}	0.005		μA typ	V_{IN} = V_{INL} or V_{INH}
		±0.1	μA max	
C_{IN}, Digital Input Capacitance	2		pF typ	
DYNAMIC CHARACTERISTICS[2]				
ADG619				
t_{ON}	80		ns typ	R_L = 300 Ω, C_L = 35 pF
	120	155	ns max	V_S = 3.3 V, Test Circuit 4
t_{OFF}	45		ns typ	R_L = 300 Ω, C_L = 35 pF
	75	90	ns max	V_S = 3.3 V, Test Circuit 4
Break-Before-Make Time Delay, t_{BBM}	40		ns typ	R_L = 300 Ω, C_L = 35 pF
		10	ns min	V_{S1} = V_{S2} = 3.3 V, Test Circuit 5
ADG620				
t_{ON}	40		ns typ	R_L = 300 Ω, C_L = 35 pF
	65	85	ns max	V_S = 3.3 V, Test Circuit 4
t_{OFF}	200		ns typ	R_L = 300 Ω, C_L = 35 pF
	330	400	ns max	V_S = 3.3 V, Test Circuit 4
Make-Before-Break Time Delay, t_{MBB}	160		ns typ	R_L = 300 Ω, C_L = 35 pF
		10	ns min	V_S = 0 V, Test Circuit 6
Charge Injection	110		pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF, Test Circuit 7
Off Isolation	–67		dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz, Test Circuit 8
Channel-to-Channel Crosstalk	–67		dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz, Test Circuit 10
Bandwidth –3 dB	190		MHz typ	R_L = 50 Ω, C_L = 5 pF, Test Circuit 9
C_S (OFF)	25		pF typ	f = 1 MHz
C_D, C_S (ON)	95		pF typ	f = 1 MHz
POWER REQUIREMENTS				V_{DD} = +5.5 V, V_{SS} = –5.5 V
I_{DD}	0.001		μA typ	Digital Inputs = 0 V or 5.5 V
		1.0	μA max	
I_{SS}	0.001		μA typ	Digital Inputs = 0 V or 5.5 V
		1.0	μA max	

NOTES
[1]Temperature ranges are as follows: B Version, –40°C to +85°C.
[2]Guaranteed by design, not subject to production test.
Specifications subject to change without notice.

SINGLE SUPPLY[1] (V_{DD} = +5 V ± 10%, V_{SS} = 0 V, GND = 0 V. All specifications –40°C to +85°C unless otherwise noted.)

Parameter	B Version +25°C	B Version –40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V_{DD}	V	V_{DD} = 4.5 V, V_{SS} = 0 V
On Resistance (R_{ON})	7		Ω typ	V_S = 0 V to 4.5 V, I_S = –10 mA,
	ß10	12.5	Ω max	Test Circuit 1
On Resistance Match Between Channels (ΔR_{ON})	0.8		Ω typ	V_S = 0 V to 4.5 V, I_S = –10 mA
	1	1.2	Ω max	
On-Resistance Flatness ($R_{FLAT(ON)}$)	0.5	0.5	Ω typ	V_S = 1.5 V to 3.3 V, I_S = –10 mA
		0.8	Ω max	
LEAKAGE CURRENTS				V_{DD} = 5.5 V
Source OFF Leakage I_S (OFF)	±0.01		nA typ	V_S = 1 V/4.5 V, V_D = 4.5 V/1 V,
	±0.25	±1	nA max	Test Circuit 2
Channel ON Leakage I_D, I_S (ON)	±0.01		nA typ	V_S = V_D = 1 V/4.5 V,
	±0.25	±1	nA max	Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current				
I_{INL} or I_{INH}	0.005		μA typ	V_{IN} = V_{INL} or V_{INH}
		±0.1	μA max	
C_{IN}, Digital Input Capacitance	2		pF typ	
DYNAMIC CHARACTERISTICS[2]				
ADG619				
t_{ON}	120		ns typ	R_L = 300 Ω, C_L = 35 pF
	220	280	ns max	V_S = 3.3 V, Test Circuit 4
t_{OFF}	50		ns typ	R_L = 300 Ω, C_L = 35 pF
	75	110	ns max	V_S = 3.3 V, Test Circuit 4
Break-Before-Make Time Delay, t_{BBM}	70		ns typ	R_L = 300 Ω, C_L = 35 pF,
		10	ns min	V_{S1} = V_{S2} = 3.3 V, Test Circuit 5
ADG620				
t_{ON}	50		ns typ	R_L = 300 Ω, C_L = 35 pF
	85	110	ns max	V_S = 3.3 V, Test Circuit 4
t_{OFF}	210		ns typ	R_L = 300 Ω, C_L = 35 pF
	340	420	ns max	V_S = 3.3 V, Test Circuit 4
Make-Before-Break Time Delay, t_{MBB}	170		ns typ	R_L = 300 Ω, C_L = 35 pF
		10	ns min	V_S = 3.3 V, Test Circuit 6
Charge Injection	6		pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF, Test Circuit 7
Off Isolation	–67		dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz, Test Circuit 8
Channel-to-Channel Crosstalk	–67		dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz, Test Circuit 10
Bandwidth –3 dB	190		MHz typ	R_L = 50 Ω, C_L = 5 pF, Test Circuit 9
C_S (OFF)	25		pF typ	f = 1 MHz
C_D, C_S (ON)	95		pF typ	f = 1 MHz
POWER REQUIREMENTS				V_{DD} = 5.5 V
I_{DD}	0.001		μA typ	Digital Inputs = 0 V or 5.5 V
		1.0	μA max	

NOTES
[1]Temperature ranges are as follows: B Version, –40°C to +85°C.
[2]Guaranteed by design, not subject to production test.
Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS[1]

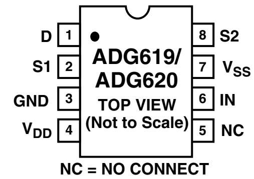
(T_A = 25°C unless otherwise noted)

V_{DD} to V_{SS} . . . . 13 V
V_{DD} to GND . . . . –0.3 V to +6.5 V
V_{SS} to GND . . . . +0.3 V to –6.5 V
Analog Inputs[2] . . . . V_{SS} –0.3 V to V_{DD} +0.3 V
Digital Inputs[2] . . . . –0.3 V to V_{DD} +0.3 V or 30 mA, Whichever Occurs First
Peak Current, S or D . . . . 100 mA (Pulsed at 1 ms, 10% Duty Cycle max)
Continuous Current, S or D . . . . 50 mA
Operating Temperature Range
  Industrial (B Version) . . . . –40°C to +85°C
Storage Temperature Range . . . . –65°C to +150°C
Junction Temperature . . . . 150°C
Micro-SOIC Package
  θ_{JA} Thermal Impedance . . . . 206°C/W
  θ_{JC} Thermal Impedance . . . . 44°C/W
SOT-23 Package
  θ_{JA} Thermal Impedance . . . . 229.6°C/W
  θ_{JC} Thermal Impedance . . . . 91.99°C/W
Lead Temperature, Soldering (10 seconds) . . . . 300°C
IR Reflow, Peak Temperature . . . . 220°C

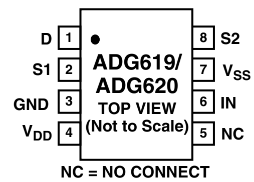
NOTES
[1]Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.
[2]Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

PIN CONFIGURATIONS

8-Lead SOT-23 (RT-8)



8-Lead Micro-SOIC (RM-8)



ORDERING GUIDE

Model	Temperature Range	Branding Information*	Package Description	Package Option
ADG619BRM	–40°C to +85°C	SVB	Micro-SOIC (microSmall Outline IC)	RM-8
ADG619BRT	–40°C to +85°C	SVB	SOT-23 (Plastic Surface Mount)	RT-8
ADG620BRM	–40°C to +85°C	SWB	Micro-SOIC (microSmall Outline IC)	RM-8
ADG620BRT	–40°C to +85°C	SWB	SOT-23 (Plastic Surface Mount)	RT-8

*Branding on SOT-23 and Micro-SOIC packages is limited to three characters due to space constraints.

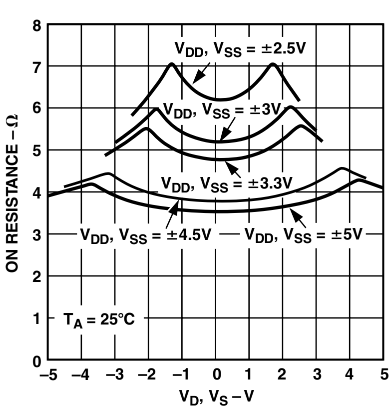
CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG619/ADG620 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

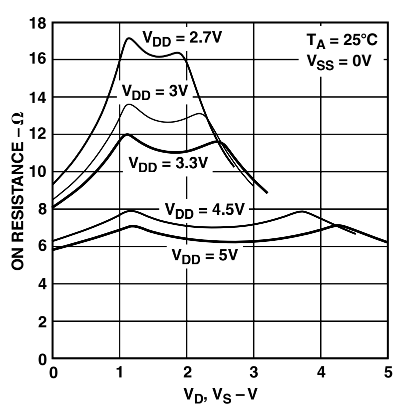
TERMINOLOGY

Mnemonic	Description
V_{DD}	Most Positive Power Supply Potential
V_{SS}	Most Negative Power Supply in a Dual Supply Application. In single supply applications, this should be tied to ground at the device.
GND	Ground (0 V) Reference
I_{DD}	Positive Supply Current
I_{SS}	Negative Supply Current
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
IN	Logic Control Input
R_{ON}	Ohmic Resistance Between D and S
DR_{ON}	On Resistance Match Between Any Two Channels, i.e., R_{ON} Max – R_{ON} Min.
$R_{FLAT(ON)}$	Flatness is Defined as the Difference Between the Maximum and Minimum Value of On Resistance as Measured Over the Specified Analog Signal Range.
I_S (OFF)	Source Leakage Current With the Switch "OFF"
I_D, I_S (ON)	Channel Leakage Current With the Switch "ON"
V_D (V_S)	Analog Voltage on Terminals D, S
V_{INL}	Maximum Input Voltage for Logic "0"
V_{INH}	Minimum Input Voltage for Logic "1"
I_{INL}(I_{INH})	Input Current of the Digital Input
C_S (OFF)	"OFF" Switch Source Capacitance
C_D, C_S (ON)	"ON" Switch Capacitance
t_{ON}	Delay Between Applying the Digital Control Input and the Output Switching On
t_{OFF}	Delay Between Applying the Digital Control Input and the Output Switching Off
t_{MBB}	"ON" Time, Measured Between the 80% Points of Both Switches, When Switching From One Address State to Another
t_{BBM}	"OFF" Time or "ON" Time Measured Between the 90% Points of Both Switches, When Switching from One Address State to Another
Charge Injection	A Measure of the Glitch Impulse Transfered From the Digital Input to the Analog Output During Switching
Crosstalk	A Measure of Unwanted Signal that is Coupled Through From One Channel to Another as a Result of Parasitic Capacitance
Off Isolation	A Measure of Unwanted Signal Coupling Through an "OFF" Switch
Bandwidth	The Frequency Response of the "ON" Switch
Insertion Loss	The Loss Due to the ON Resistance of the Switch

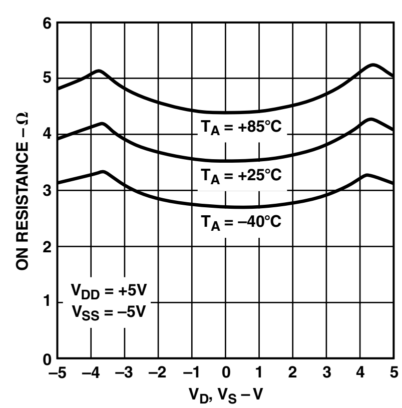
Typical Performance Characteristics



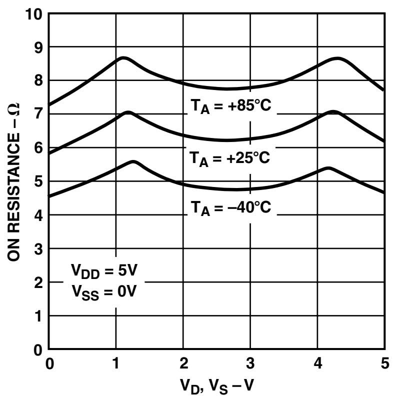
TPC 1. On Resistance vs. V_D (V_S) – Dual Supply



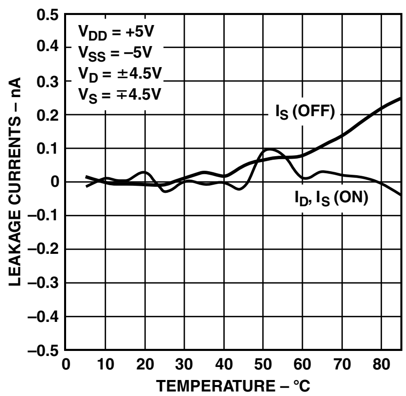
TPC 2. On Resistance vs. V_D (V_S) – Single Supply



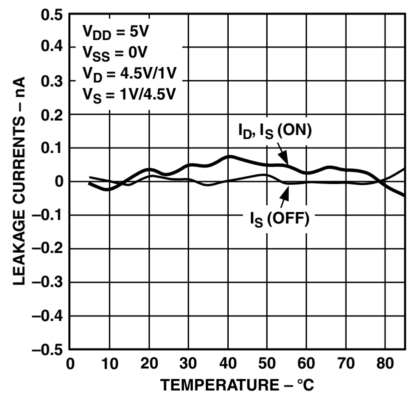
TPC 3. On Resistance vs. V_D (V_S) for Different Temperatures – Dual Supply



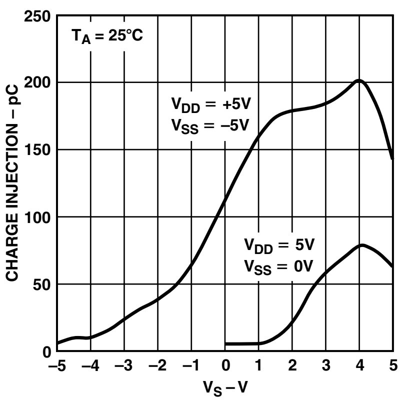
TPC 4. On Resistance vs. V_D (V_S) for Different Temperatures – Single Supply



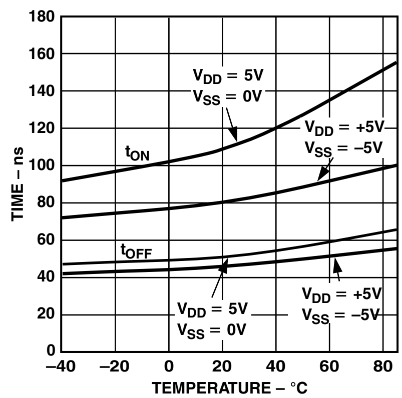
TPC 5. Leakage Currents vs. Temperature – Dual Supply



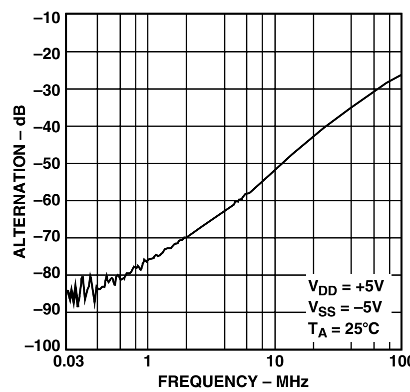
TPC 6. Leakage Currents vs. Temperature – Single Supply



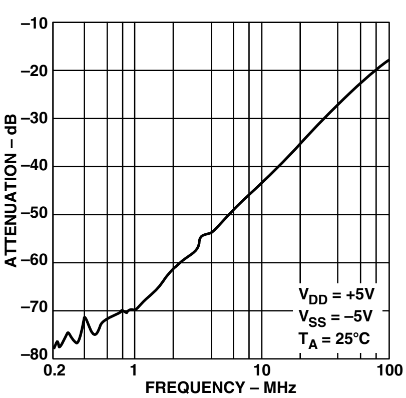
TPC 7. Charge Injection vs. Source Voltage



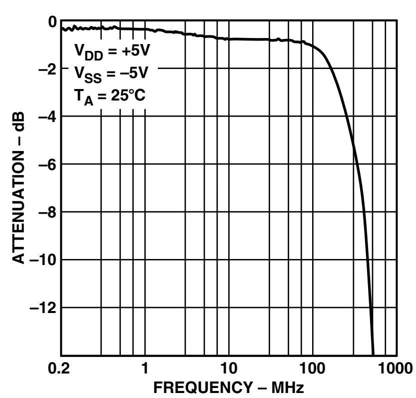
TPC 8. t_{ON}/t_{OFF} Times vs. Temperature



TPC 9. Off Isolation vs. Frequency

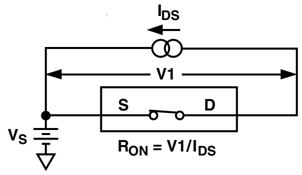


TPC 10. Crosstalk vs. Frequency

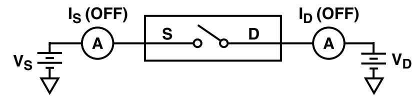


TPC 11. On Response vs. Frequency

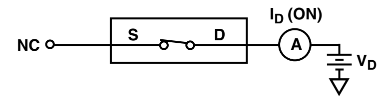
TEST CIRCUITS



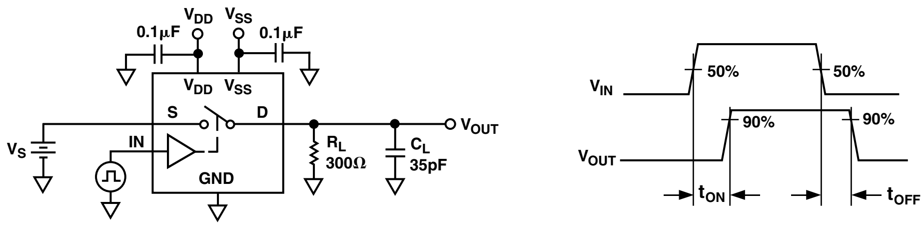
Test Circuit 1. On Resistance



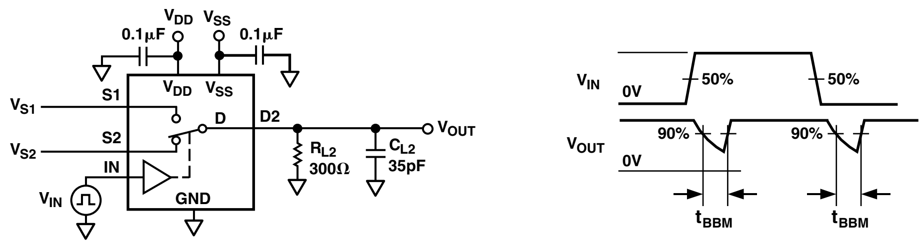
Test Circuit 2. Off Leakage



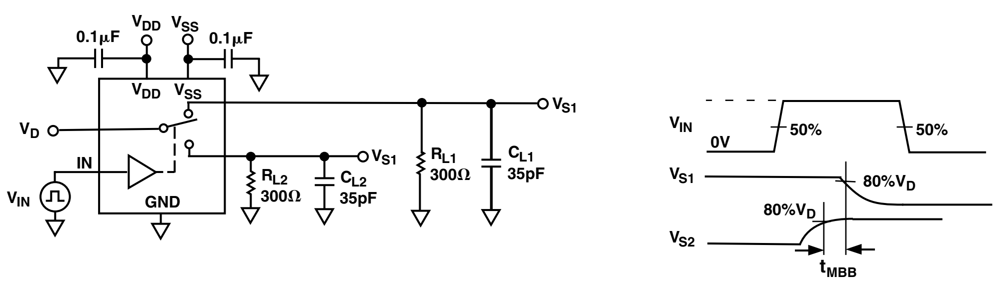
Test Circuit 3. On Leakage



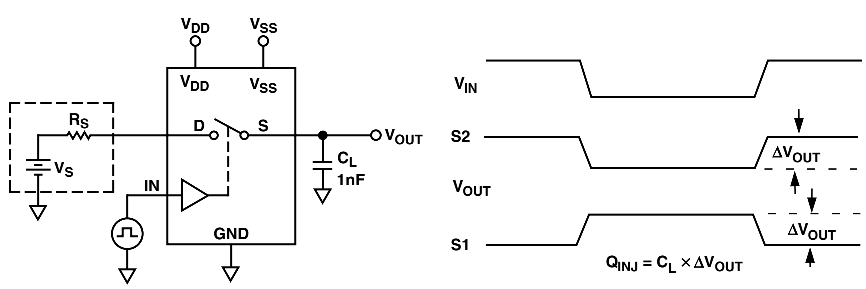
Test Circuit 4. Switching Times



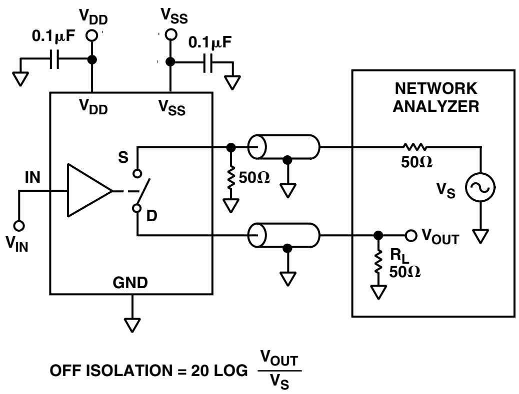
Test Circuit 5. Break-Before-Make Time Delay, t_{BBM} (ADG619 Only)



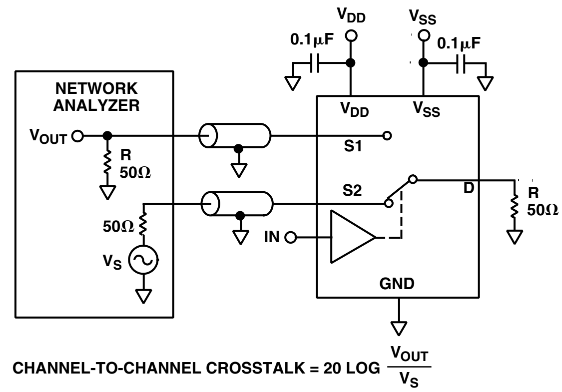
Test Circuit 6. Make-Before-Break Time Delay, t_{MBB} (ADG620 Only)



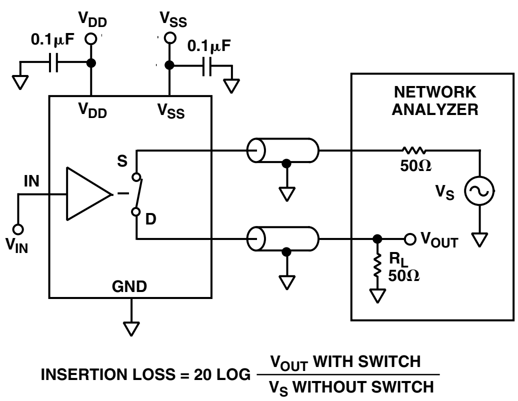
Test Circuit 7. Charge Injection



Test Circuit 8. Off Isolation



Test Circuit 10. Channel-to-Channel Crosstalk

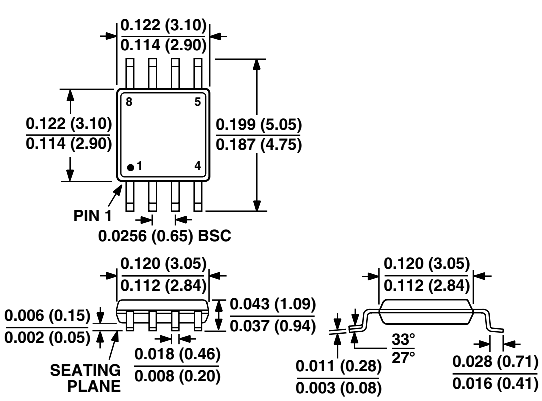


Test Circuit 9. Bandwidth

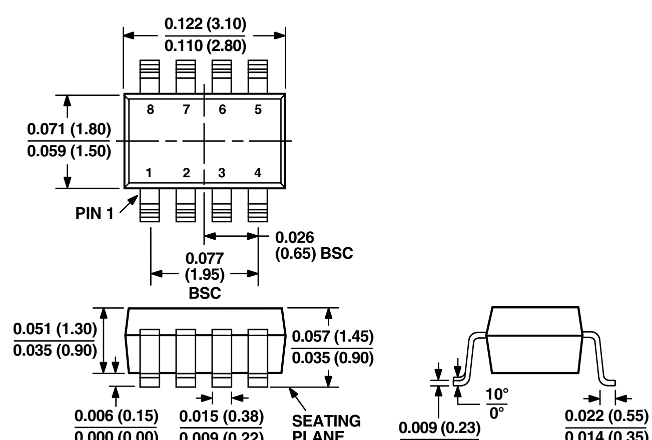
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

8-Lead Micro-SOIC Package (RM-8)



8-Lead Plastic Surface Mount Package (RT-8)



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